TOSHIBA TLP747GF

## TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-THYRISTOR

## **TLP747GF**

**OFFICE MACHINE** SWITCHING POWER SUPPLY

The TOSHIBA TLP747GF consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

All parameters are tested to the specification of TLP747G. (both condition and limits)

Peak Off-State Voltage: 400V Min. Trigger LED Current : 15mA Max. On-State Current : 150mA Max.

UL Recognized : UL1577, File No. E67349

**BSI** Approved : BS EN60065:1994

> Certificate No. 7364 BS EN60950:1992 Certificate No. 7365

: SS4330784, Certificate No. 9325163 SEMKO Approved

No. 9522142

Isolation Voltage : 4000Vrms Min.

Option (D4) type

VDE Approved : DIN VDE0884/06.92,

Certificate No. 74286, 91808

Maximum Operating Insulation Voltage: 890, 1130Vpk Highest Permissible Over Voltage 6000, 8000VpK

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

Creepage Distance : 8.0mm (Min.) Clearance : 8.0mm (Min.) Internal Creepage Path: 4.0mm (Min.) Insulation Thickness : 0.5mm

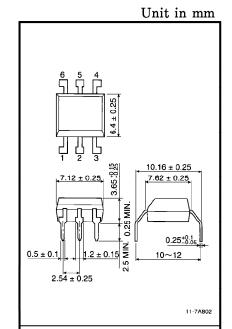
Conforming Safety Standards:

DIN 57 804.VDE0804/1.83 DIN IEC65/VDE0860/8.81 DIN IEC380/VDE0806/8.81

DIN IEC435/VDE0805/Draft Nov.84

DIN IEC601T1 / VDE0750T1 / 5.82

BS7002: 1989 (EN60950)

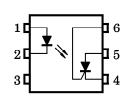


Weight: 0.42g

TOSHIBA

PIN CONFIGURATIONS (TOP VIEW)

11-7A802



1: ANODE

2: CATHODE

3: NC

4 : CATHODE 5: ANODE

6: GATE

961001EBC2

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Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

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